

TOSHIBA CCD LINEAR IMAGE SENSOR CCD(Charge Coupled Device)

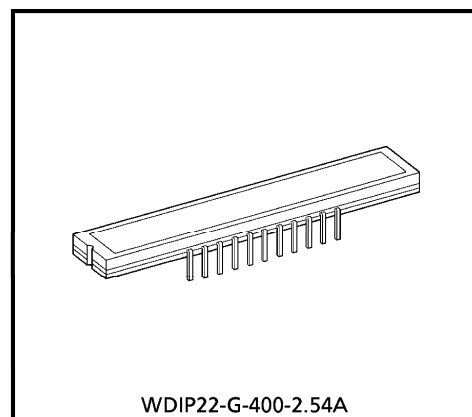
TCD1208AP

The TCD1208AP is a high sensitive and low dark current 2160- element image sensor. The sensor can be used for facsimile, imagescanner and OCR. The device contains a row of 2160 photodiodes, which provide a 8 lines/mm (200 DPI) across a B4 size paper. The device is operated by 5V (pulse), and 5V power supply.

FEATURES

- Number of Image Sensing Elements : 2160
- Image Sensing Element Size : 14 μ m by 14 μ m on 14 μ m centers
- Photo Sensing Region : High sensitive, Low dark current
- Clock : 2 phase (5V)
- Package : 22 pin DIP (T-CAPP)

TOSHIBA-CCD-ADVANCED-PLASTIC-PACKAGE



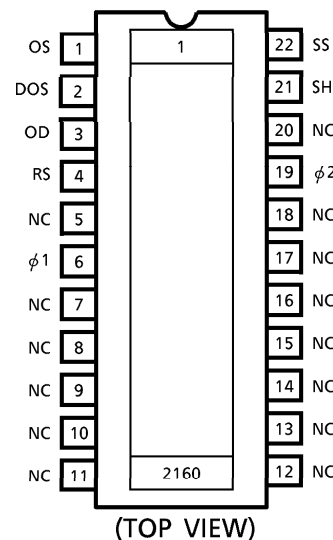
Weight : 2.7g (Typ.)

MAXIMUM RATINGS (Note 1)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Clock Pulse Voltage	V_{ϕ}	- 0.3~8	V
Shift Pulse Voltage	V_{SH}		
Reset Pulse Voltage	V_{RS}		
Power Supply Voltage	V_{OD}		
Operating Temperature	T_{opr}	- 25~60	°C
Storage Temperature	T_{stg}	- 40~100	°C

(Note 1) All voltage are with respect to SS terminals (Ground).

PIN CONNECTIONS

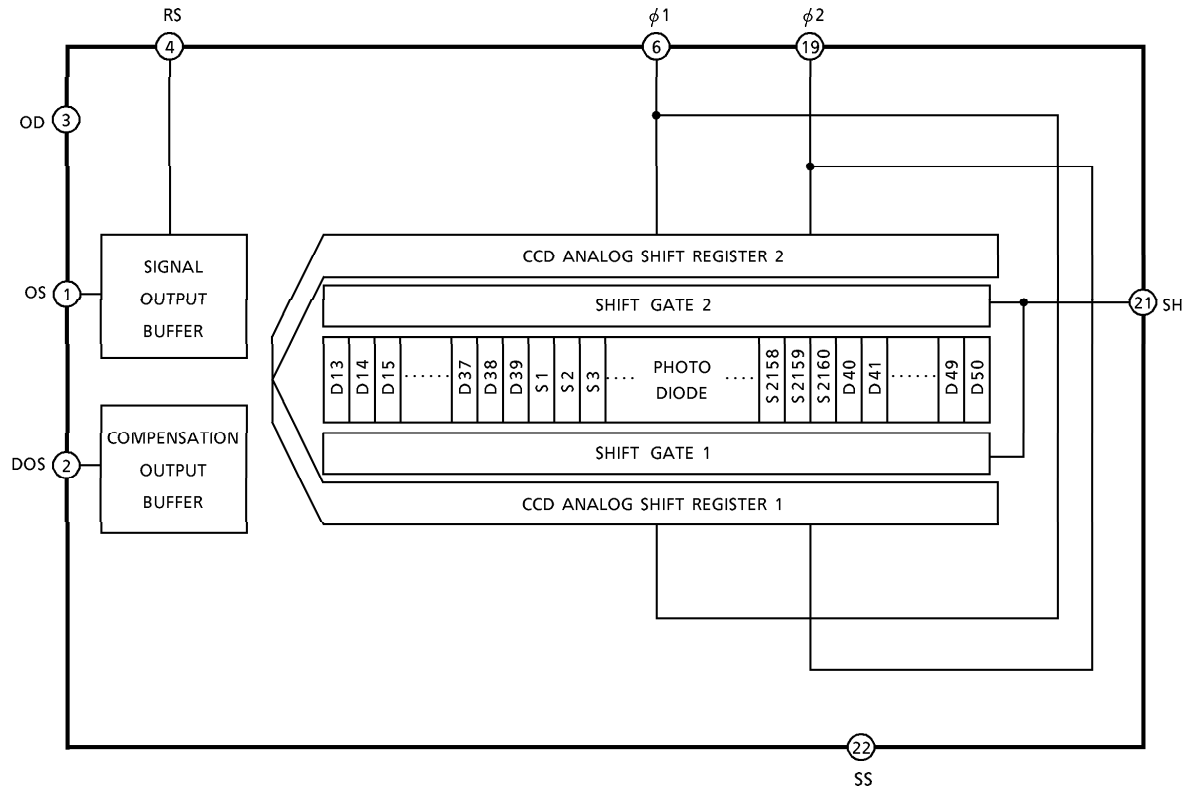


(TOP VIEW)

961001EBA1

- TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.
- The products described in this document are subject to foreign exchange and foreign trade control laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

CIRCUIT DIAGRAM



PIN NAMES

$\phi 1$	Clock (Phase 1)
$\phi 2$	Clock (Phase 2)
SH	Shift Gate
RS	Reset Gate
OS	Signal Output
DOS	Compensation Output
OD	Power
SS	Ground
NC	Non Connection

OPTICAL / ELECTRICAL CHARACTERISTICS

(Ta = 25°C, V_{OD} = 5V, V_φ = V_{SH} = V_{RS} = 5V (PULSE), f_φ = 0.5MHz, f_{RS} = 1MHz, LOAD RESISTANCE = 100kΩ, t_{INT} (INTEGRATION TIME) = 10ms, LIGHT SOURCE = DAYLIGHT FLUORESCENT LAMP)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Sensitivity	R	82	110	138	V/lx·s	(Note 2)
Photo Response Non Uniformity	PRNU (1)	—	—	10	%	(Note 3)
	PRNU (3)	—	7	16	mV	(Note 10)
Register Imbalance	RI	—	—	3	%	(Note 4)
Saturation Output Voltage	V _{SAT}	0.6	1.5	—	V	(Note 5)
Saturation Exposure	SE	—	0.01	—	lx·s	(Note 6)
Dark Signal Voltage	V _{DRK}	—	2	6	mV	(Note 7)
Dark Signal Non Uniformity	DSNU	—	3	7	mV	(Note 7)
DC Power Dissipation	P _D	—	50	100	mW	
Total Transfer Efficiency	TTE	92	—	—	%	
Output Impedance	Z _O	—	—	1	kΩ	
Dynamic Range	DR	—	750	—	—	(Note 8)
DC Signal Output Voltage	V _{OS}	3	3.5	4.5	V	(Note 9)
DC Compensation Output Voltage	V _{DOS}	3	3.5	4.5	V	(Note 9)
DC Mismatch Voltage	V _{OS} -V _{DOS}	—	50	100	mV	(Note 11)
Random Noise	ND _σ	—	1.7	—	mV	(Note 12)

(Note 2) Sensitivity for 2854K W-Lamp is 330V/lx·s(Typ.)
Sensitivity for LED (567nm) is 71V/lx·s(Typ.)

(Note 3) Measured at 50% of SE (Typ.)

$$\text{Definition of PRNU: } \text{PRNU} = \frac{\Delta\chi}{\bar{\chi}} \times 100 (\%)$$

Where $\bar{\chi}$ is average of total signal outputs and $\Delta\chi$ is the maximum deviation from $\bar{\chi}$ under uniform illumination.

(Note 4) Measured at 50% of SE (Typ.)

RI is defined as follows:

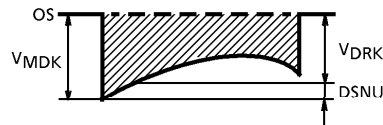
$$\text{RI} = \frac{\sum_{n=1}^{2159} |\chi_n - \chi_{n+1}|}{2159 \times \bar{\chi}} \times 100 (\%)$$

Where χ_n and χ_{n+1} are signal outputs of each pixel. $\bar{\chi}$ is average of total signal outputs.

(Note 5) V_{SAT} is defined as minimum Saturation Output Voltage of all effective pixels.

(Note 6) Definition of SE : SE = $\frac{V_{SAT}}{R}$

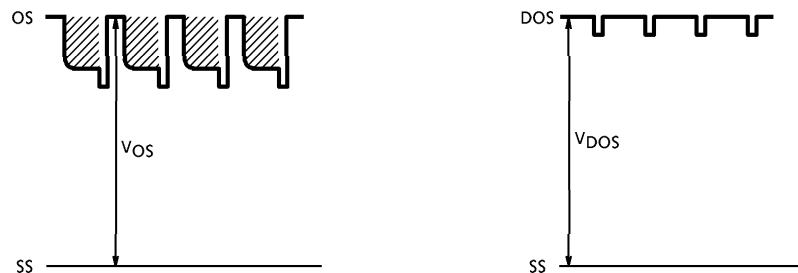
(Note 7) V_{DRK} is defined as average dark signal voltage of all effective pixels. DSNU is defined as different voltage between V_{DRK} and V_{MDK} , when V_{MDK} is maximum dark voltage.



(Note 8) Definition of DR : $DR = \frac{V_{SAT}}{V_{DRK}}$

V_{DRK} is proportional to t_{INT} (Integration time). So the shorter t_{INT} is, the wider DR is.

(Note 9) DC Signal Output Voltage and DC Compensation Output Voltage are defined as follows:



(Note 10) PRNU (3) is defined as maximum voltage with next pixel where measured 5% of SE (Typ.).

(Note 11) $V_{OD} = 4.7V$ DC Mismatch Voltage.

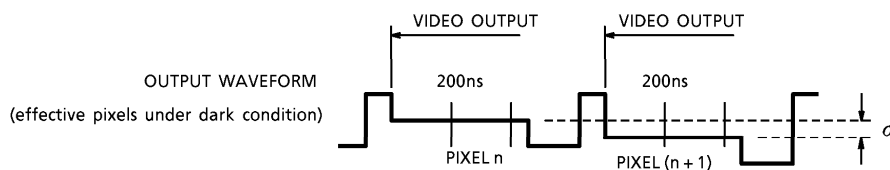
(Note 12)

1. DEFINITION

Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure.

2. CALCULATION PROCEDURE

The following is the calculation procedure of random noise.



- 1) Two adjacent pixels (pixel n and n + 1) in one reading are fixed as measurement points.
- 2) Each of the output levels at video output period is averaged over 200 nanosecond period to get V_n and V_{n+1} .
- 3) V_{n+1} is subtracted from V_n to get ΔV .

$$\Delta V = V_n - V_{n+1}$$
- 4) The standard deviation of ΔV is calculated after procedure 2) and 3) are repeated 30 times (30 readings).

$$\overline{\Delta V} = \frac{1}{30} \sum_{i=1}^{30} |\Delta V_i| \quad \sigma = \sqrt{\frac{1}{30} \sum_{j=1}^{30} (|\Delta V_j| - \overline{\Delta V})^2}$$

- 5) Procedure 2), 3) and 4) are repeated 10 times to get 10 sigma values.

$$\overline{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

- 6) $\overline{\sigma}$ value calculated using the above procedure is observed $\sqrt{2}$ times larger than that measured relative to the ground level. So we specify the random noise as the following.

$$\text{Random noise } (N_{D\sigma}) = \frac{1}{\sqrt{2}} \overline{\sigma}$$

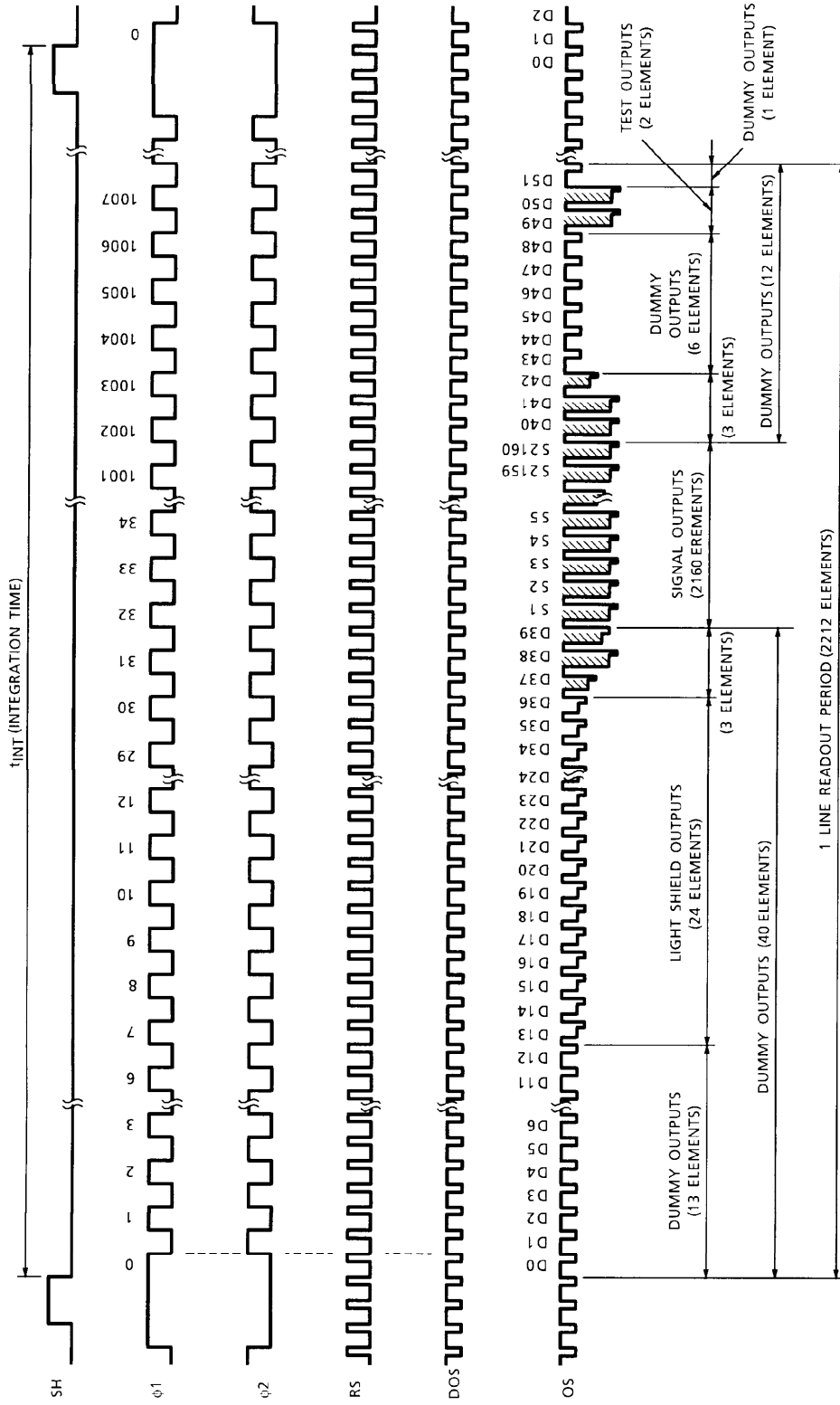
OPERATING CONDITION

CHARACTERISTIC		SYMBOL	MIN.	TYP.	MAX.	UNIT
Clock Pulse Voltage	"H" Level	V_{ϕ}	4.5	5	5.5	V
	"L" Level		0	0	0.3	
Shift Pulse Voltage	"H" Level	V_{SH}	4.5	5	5.5	V
	"L" Level		0	0	0.3	
Reset Pulse Voltage	"H" Level	V_{RS}	4.7	5	5.5	V
	"L" Level		0	0	0.3	
Power Supply Voltage		V_{OD}	4.7	5.0	5.3	V

CLOCK CHARACTERISTICS (Ta = 25°C)

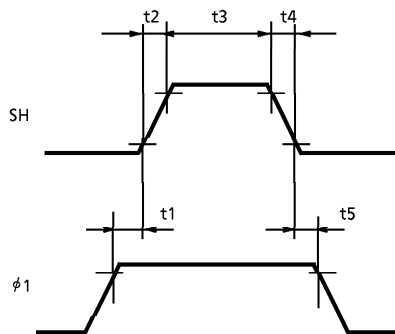
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Clock Pulse Frequency	f_{ϕ}	0.15	0.5	1.0	MHz
Reset Pulse Frequency	f_{RS}	0.3	1.0	2.0	MHz
Clock Capacitance	C_{ϕ}	—	200	300	pF
Shift Gate Capacitance	C_{SH}	—	100	200	pF
Reset Gate Capacitance	C_{RS}	—	10	30	pF

TIMING CHART

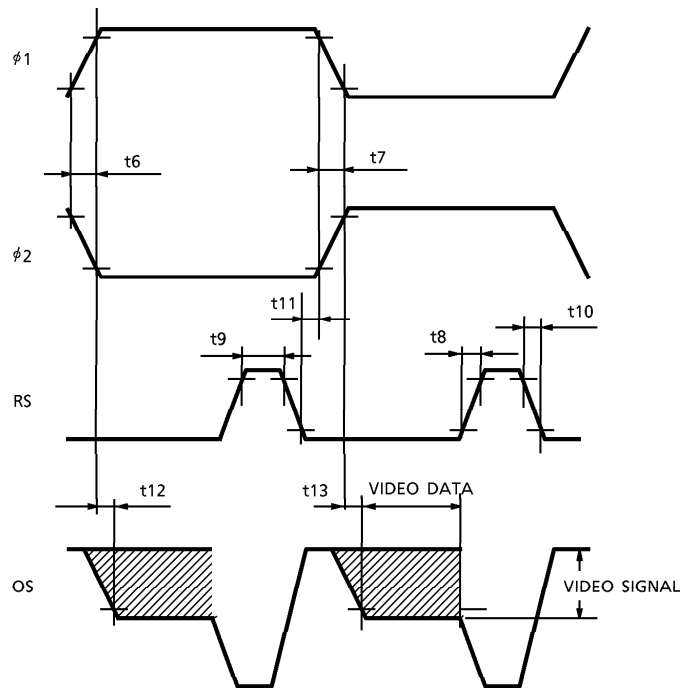


TIMING REQUIREMENTS

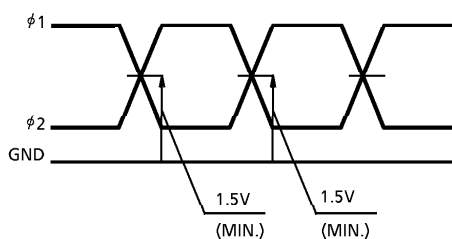
SH, $\phi 1$ Timing



$\phi 1, \phi 2, RS, OS$ Timing



$\phi 1, \phi 2$ Cross Point

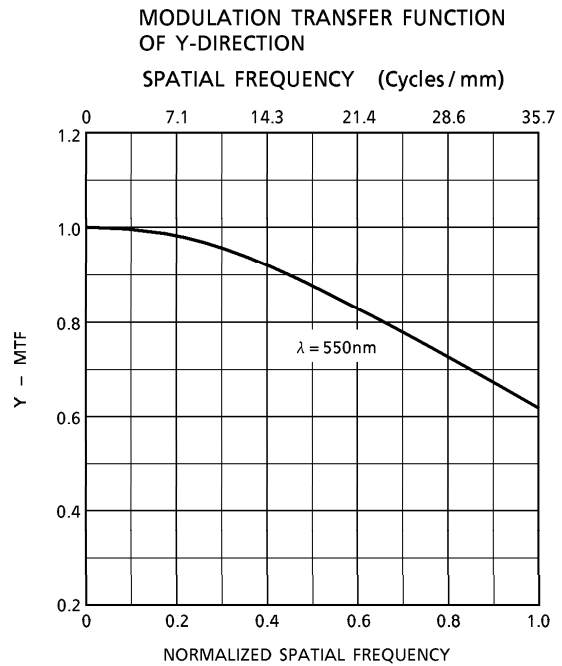
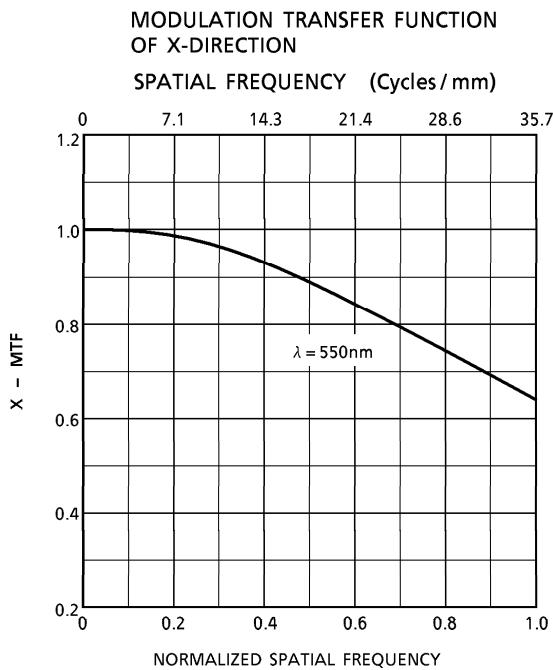
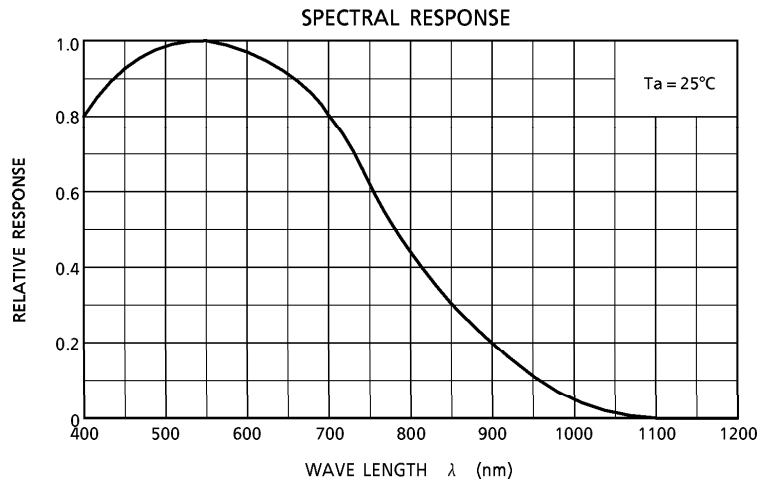


CHARACTERISTIC	SYMBOL	MIN.	TYP. (Note 13)	MAX.	UNIT
Pulse Timing of SH and $\phi 1$	t1, t5	0	100	—	ns
SH Pulse Rise Time, Fall Time	t2, t4	0	50	—	ns
SH Pulse Width	t3	500	1000	—	ns
$\phi 1, \phi 2$ Pulse Rise Time, Fall Time	t6, t7	0	60	100	ns
RS Pulse Rise Time, Fall Time	t8, t10	0	20	—	ns
RS Pulse Width	t9	40	250	—	ns
Pulse Timing of $\phi 1, \phi 2$ and RS	t11	230	—	—	ns
Video Data Delay Time (Note 14)	t12, t13	—	150	—	ns

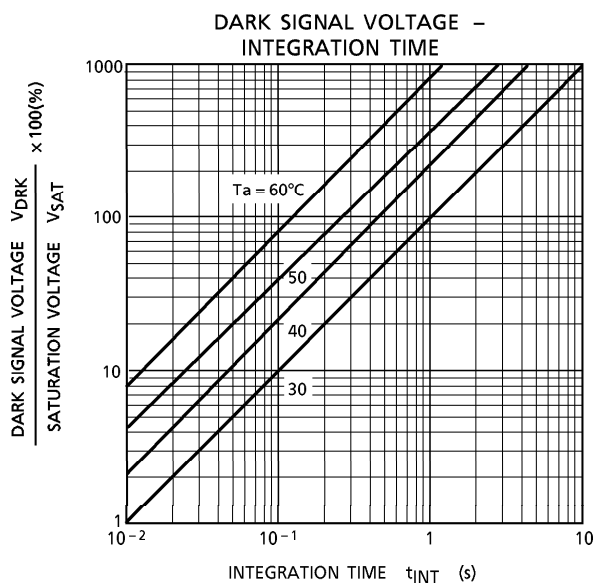
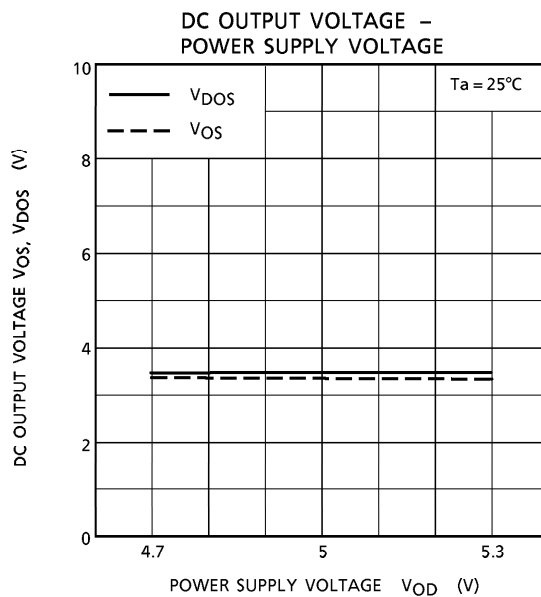
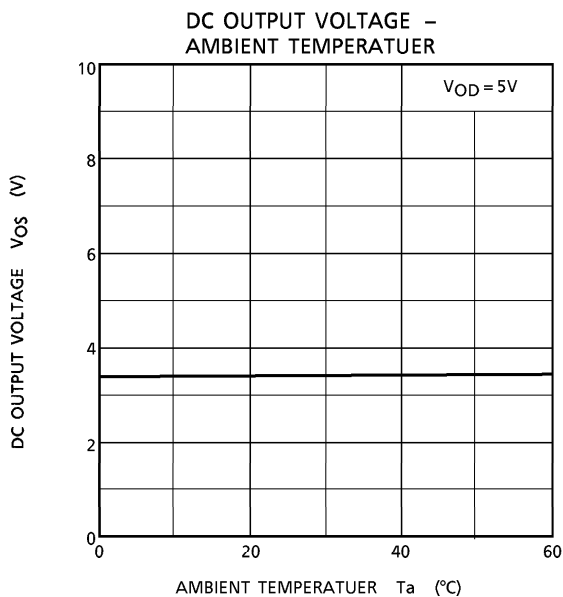
(Note 13) TYP. is the case of $f_{RS} = 1\text{MHz}$

(Note 14) Load Resistance is $100\text{k}\Omega$

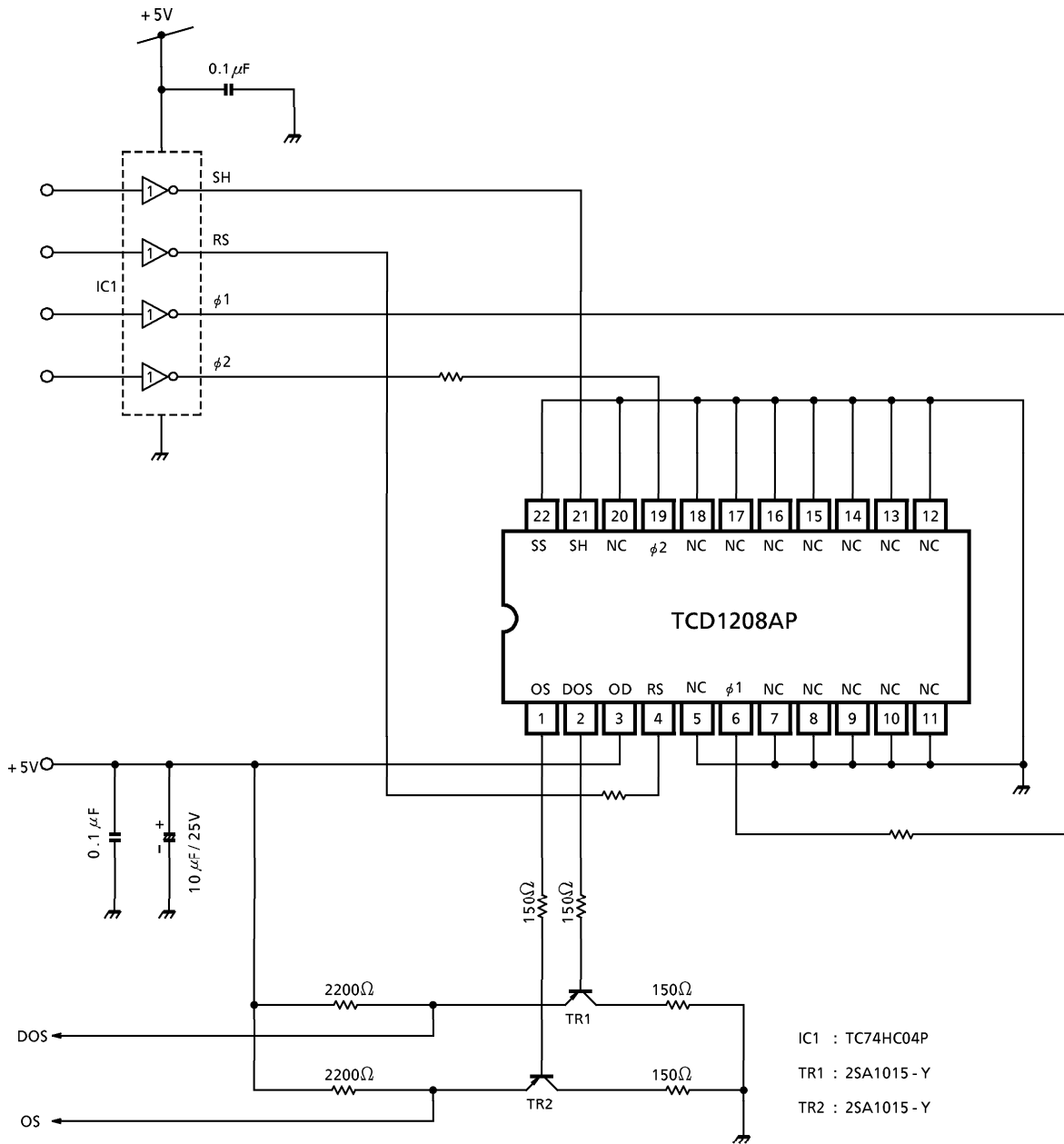
TYPICAL PERFORMANCE CURVES



TYPICAL PERFORMANCE CURVES



TYPICAL DRIVE CIRCUIT



CAUTION**1. Window Glass**

The dust and stain on the glass window of the package degrade optical performance of CCD sensor.

Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N₂.

Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

2. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

3. Incident Light

CCD sensor is sensitive to infrared light.

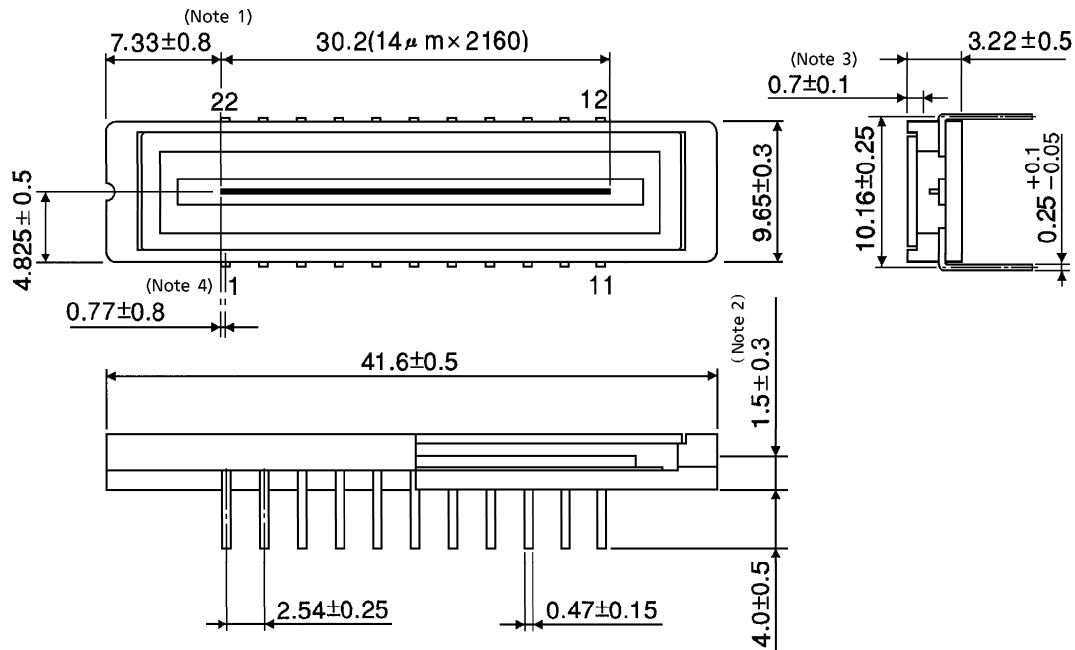
Note that infrared light component degrades resolution and PRNU of CCD sensor.

4. Lead Frame Forming

Since this package is not stout against mechanical stress, you should not reform the lead frame. We recommend to use a IC-inserter when you assemble to PCB.

OUTLINE DRAWING
WDIP22-G-400-2.54A

Unit : mm



- (Note 1) No. 1 SENSOR ELEMENT (S1) TO EDGE OF PACKAGE.
- (Note 2) TOP OF CHIP TO BOTTOM OF PACKAGE.
- (Note 3) GLASS THICKNES (n = 1.5)
- (Note 4) No. 1 SENSOR ELEMENT (S1) TO CENTER OF No. 1 PIN.

Weight : 2.7g (Typ.)